Mike Bond

INEX

An Introduction to INEX and in particular high power RF and microwave devices in single crystal diamond





Established in 2002, INEX is a commercial, customer focussed organisation, owned







INEX

- · Research,
- Development,
- Prototyping,
- Manufacturing,

for your electronic devices and Microsystems within an ISO9001:2000 certified environment.



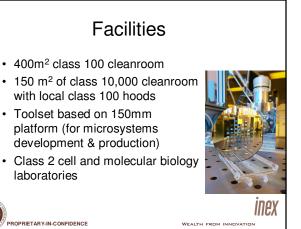


INEX works across all markets and in these particular business areas

- Diamond
- Compound Semiconductors
- Microsystems
- Integrated Life Sciences













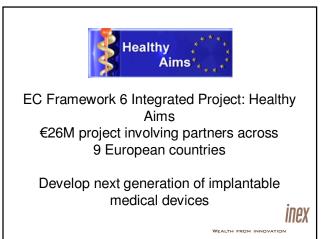
INEX, owned by
Newcastle University, can provide an
important role within Regional,
National and Internationally Funded
projects.

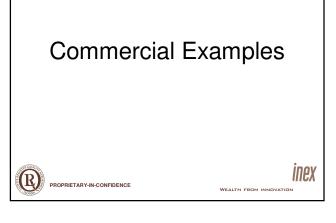


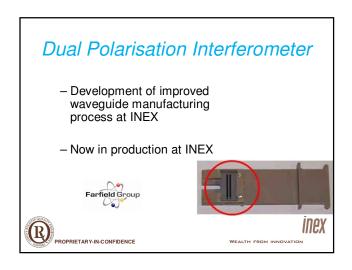




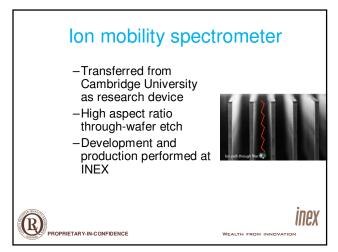












Medical parameter measurement device

- INEX developed production prototypes for clinical testing
- Now transferring to volume production in 200mm foundry off-shore







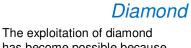
Compound Semiconductors

- InP pHEMT and associated passives
- · GaN device processing
- · GaAs device processing
 - Manufactured GaAs Hall Sensors in the region of 80,000 devices per week
 - Very high yields

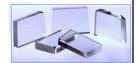








has become possible because of breakthroughs in diamond synthesis technology, specifically chemical vapour deposition, CVD, that has enabled single crystal diamond to be manufactured with the high purity and consistency required.



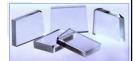
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Diamond

Diamond as an electrochemical and biological material.

Diamond is a bio-inert and biocompatible material and is ideal for the fabrication of in vivo sensors and electrodes. INEX are active in this field







Diamond

Diamond as an optical material.

Diamond is transparent from the X-ray through the visible and infrared regions of the electromagnetic spectrum. This property combined with high strength and thermal shock make it ideal for X-ray monitors.



NEX is active in this field

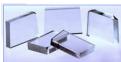


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Diamond

Diamond as an electronic material.

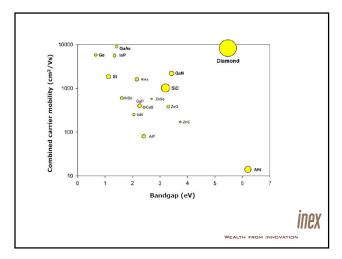
Diamond is a wide bandgap semiconductor and has excellent intrinsic electronic properties especially for high power and frequency applications. For extreme demand applications, single crystal diamond devices are superior to other materials including silicon and gallium arsenide











Diamond

Very high power RF & microwave devices in single crystal diamond

12 August 2009 Press Release

"£3M Diamond Electronics Development Project wins Technology Strategy Board Funding"

- •Diamond Microwave Devices Ltd (DMD)
- •INEX
- •Element Six Ltd,
- •MBDA UK Ltd
- •University of Sheffield.





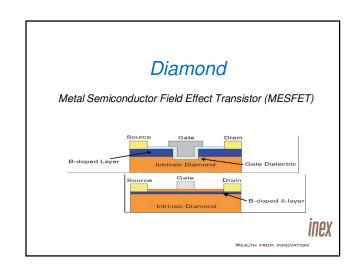
Diamond

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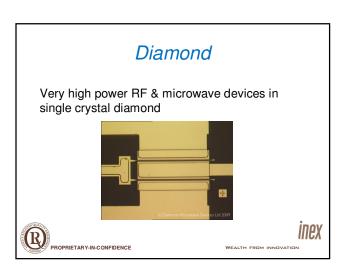




Diamond Very high power RF & microwave devices in single crystal diamond 12 August 2009 Press Release "£3M Diamond Electronics Development Project wins Technology Strategy Board Funding" • Diamond Microwave Devices Ltd (DMD) • INEX • Element Six Ltd, • MBDA UK Ltd • University of Sheffield.







Diamond

INEX have been working with diamond for many years now and has several development devices in progress.

We cannot die to CONFIDENTIALITY discuss in open forum the full extent of these developments, but we are under NDA prepared to hold one on one discussions for future developments.



WEALTH FROM INNOVATION

Mike Bond

INEX

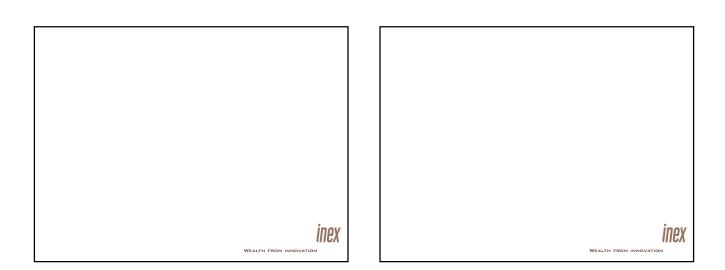
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WEALTH FROM INNOVATION



Capabilities to provide solutions



Capabilities

Substrates:

- 150 mm silicon, SOI, glass and quartz wafers (standard)
- 100/75 mm silicon, SOI, glass and quartz wafers
- · Single wafers or bonded pairs
- Irregular/small substrates (e.g. diamond)
- · Polyimide film and other flexible substrates

Design and Modelling:

- Mask layout (L-Edit, AutoCAD)
- FEA modelling (Ansys)



Capabilities

Lithography:

- Single and double-sided contact aligners (1:1)
 - Minimum feature size: 2.5 μm
- Alignment accuracy \pm 1 μm (front side align), $\pm 2~\mu m$ (front to back align) Stepper (1:1) Minimum feature size: ~1 μm
- Overlay accuracy: 0.16 μm
 E-beam writer:
 - · Minimum feature size ~100 nm

- Overlay & stitching accuracy ~60 nm HMDS vapour priming Spin coating of photoresists and polyamides
- Puddle, spray or tank development
- Hotplate and oven baking Deep UV resist treatment
- Lift-off process (image reversal and bi-layer)



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Capabilities

EVG TOOLING

- •Resist Coater
- Resist Developer
- · Wafer Wash







Capabilities

- Plasma Etching:
 DRIE of silicon (Bosch process)
 DRIE of silicon dioxide and glass (ICP source)
 RIE of silicon dioxide, nitride, poly-silicon, polyimide and PZT
 Metal etching (ICP source)
 Emission and optical end-point detectors

 - Resist stripping and descum

- Metallisation:

 Balzers BAK550 e-beam evaporator
 Cr, Nickel, NiCr, Au, Ti, Cu, Pt

 Nordiko sputterer
 Cr, Au, Ti, Tiw', Cu, NiCr (Other Metals, targets required)

 MRC943 (3 Planar DC/RF Magnetron Sputtering Cathodes)
 Al, Ti, Au', Tiw', Alw', Tiwk'' (Other Metals, targets required)

 DC and pulse plating of metals (Au, Ni, Pt and Cu)



Capabilities STS Equipment · Advanced Silicon Etch · Advanced Oxide Etch • PECVD WEALTH FROM INNOVATION



Capabilities

Wafer Bonding:

- Ultrasonic wafer cleaning station Silicon fusion bonding

- Anodic bonding
 Adhesive wafer bonding
 Bonding at atmospheric pressure or vacuum (to 10-5 mbar)
 Aligned wafer bonding with < 10 µm accuracy

- Wet Processing:
 Dedicated wet process stations for solvent, acid and alkali processing Anisotropic silicon etching (TMAH and KOH)

- His etching of silicon dioxide and glass Wet etching of metals (e.g. Ti, Cr, Au, Cu, NiCr and Al) Wafer cleaning (RCA, Piranha and solvent) Solvent tools for lift-off and resist stripping

- Photo-mask cleaning HF release etch
- Supercritical CO2 drying



Capabilities

Back-End, Assembly and Packaging:

- · Wafer dicing (glass, silicon and ceramic substrates)
- Wire bonding Wedge Al and Au Ball
- · Bond pull/shear testing
- Flip chip bonding (Pb/Sn and Pb-free)
- · Die bonding
- · CNC Micro Milling of Ceramic, Glass & Polymer materials with minimum feature sizes of 50 μm



Capabilities **CNC Micro-Miller**





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Capabilities

Thermal Processing:

- Wet oxidation of silicon
- Dry oxidation of silicon High temperature anneal (N_2 or O_2 atmosphere)

CVD Processing:

- LPCVD deposition of poly and amorphous silicon (un-doped)
 High and low frequency PECVD deposition of silicon oxide, nitride oxynitride and amorphous silicon
 Mixed frequency PECVD deposition of silicon nitride (low stress)

- - PDMS casting
 - Polymer micro-milling



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Capabilities

Metrology, Inspection and Characterisation:

- Inspection
 Optica
 Scann Optical microscopy
 Scanning electron microscopy
- Metrology
 - Spectroscopic ellipsometry (film thickness and RI)
 - Reflectance spectrometry (film thickness) Prism coupling (RI measurement) Line width and CD measurement

 - Wafer thickness, bow and stress measurement

 - Bulk and sheet resistivityStylus profilometry (step height and surface roughness)
- Characterisation
 - FTIR spectrometery
 Raman spectrometry

 - EDAX
 - Scanning probe microscopy (AFM & STM)
 - Contact angle measurement



Capabilities

Process Specific Capabilities:

- Multi material dry etching (Diamond, ITO, PZT, in development GaAs, InP, GaN)
- · Air Bridge processing
- Schottky and Ohmic contact metallisation schemes (Targeting specific contact resistances)
- DUV resist technologies
- Processing of RF micro-bridge structures
- Multi Metal microstrip fabrication
- Optically deposited SiON layers to high specification tolerances
- Thick film SiO2 etching
- Smooth faceted end face for the optical waveguide
- Through wafer wet etching of glass/pyrex using a-Si masking layer
- Processing of flexible substrates, with multi lith steps



Capabilities

Process Specific Capabilities:

- DC Electrical testing a) Two terminal testing measuring channel conduction, and for determining isolation; b) Three-terminal testing to test the voltage applied to the gate to modulate the current-voltage characteristic of the channel.
- Multi wafer processing of anodic bonded silicon wafers creating 2µm membranes, 100µm diameter over a cavity
- Silicon cantilevers $10\mu m$ thick and several millimetres in size of various shapes with minimum features down to 2µm.
- Handling and processing of 100 μm thick Si substrates, anodic bonding and alignment to within 10 μm .
- Anodic release of actuated cantilevers using multi-layer polymer
- Release process to fabricate 1mm long, 20µm thick neural electrodes
- Device glass encapsulation using triple stack anodic bonding
- · BCB wafer scale bonding



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